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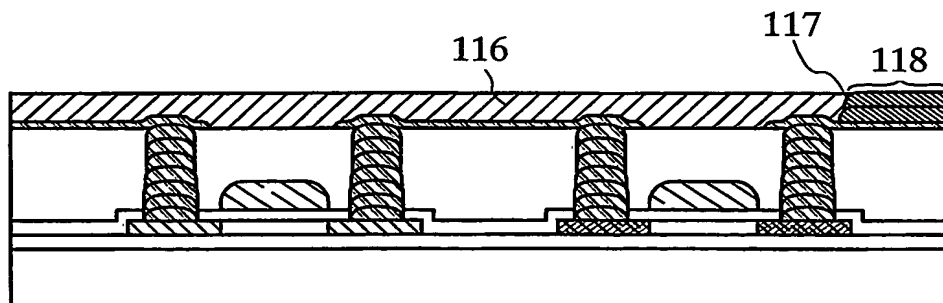
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(54) Title: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: An IC card is more expensive than a magnetic card, and an electronic tag is also more expensive as a substitute for bar codes. Therefore, the present invention provides an extremely thin integrated circuit that can be mass-produced at low cost unlike a chip of a conventional silicon wafer, and a manufacturing method thereof. One feature of the present invention is that a thin integrated circuit is formed by a formation method that can form a pattern selectively, on a glass substrate, a quartz substrate, a stainless substrate, a substrate made of synthetic resin having flexibility, such as acryl, or the like except for a bulk substrate. Further, another feature of the present invention is that an ID chip in which a thin film integrated circuit and an antenna according to the present invention are mounted is formed.